

IGBT Die

Features

- ## Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^{\circ}\text{C}$	V_{CE}	650	V
DC Collector Current, limited by $T_{J(\text{max})}$	I_C	(Note 1)	A
Pulsed Collector Current (Note 2)	$I_{C, \text{pulse}}$	120	A
Gate–Emitter Voltage	V_{GE}	± 20	V
Maximum Junction Temperature	T_J	-55 to $+175$	$^{\circ}\text{C}$
Short Circuit Withstand Time, $V_{GE} = 15 \text{ V}$, $V_{CE} = 400\text{V}$, $T_J \leq 150^{\circ}\text{C}$	T_{SC}	5.0	μs

1. Depending on thermal properties of assembly.
2. T_{pulse} limited by T_{imax} , 5.0 μs pulse, $V_{\text{GE}} = 15 \text{ V}$.

Parameter	Value	Unit
Die Size	3550 x 3550	μm^2
Emitter Pad Size	See die layout	μm^2
Gate Pad Size	410 x 670	μm^2
Die Thickness	3	mils
Wafer Size	150	mm
Top Metal	4 μm AlSi	
Back Metal	2 μm TiNiAg	
Max possible chips per wafer	996	
Passivation frontside	Oxide–Nitride	
Reject ink dot size	25 mils	
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Die on tape in ring-pack Storage time: < 3 months	

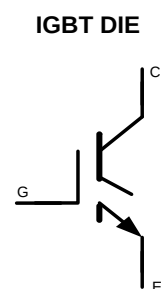
Device	Inking?	Shipping
NGTD13T65F2WP	Yes	Bare Wafer on Tape
NGTD13T65F2SWK	Yes	Sawn Wafer on Tape



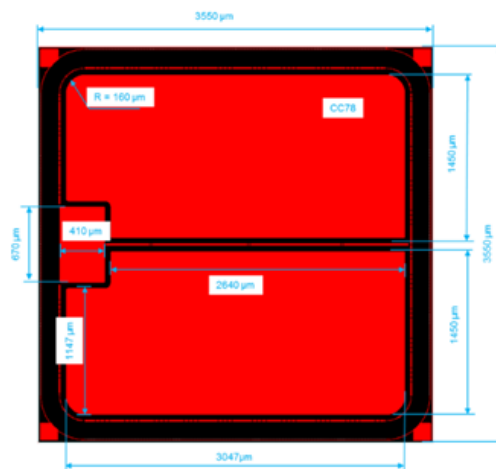
ON Semiconductor®

www.onsemi.com

$V_{RCE} = 650 \text{ V}$
 $I_C = \text{Limited by } T_{J(\text{max})}$



DIE OUTLINE



NGTD13T65F2

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

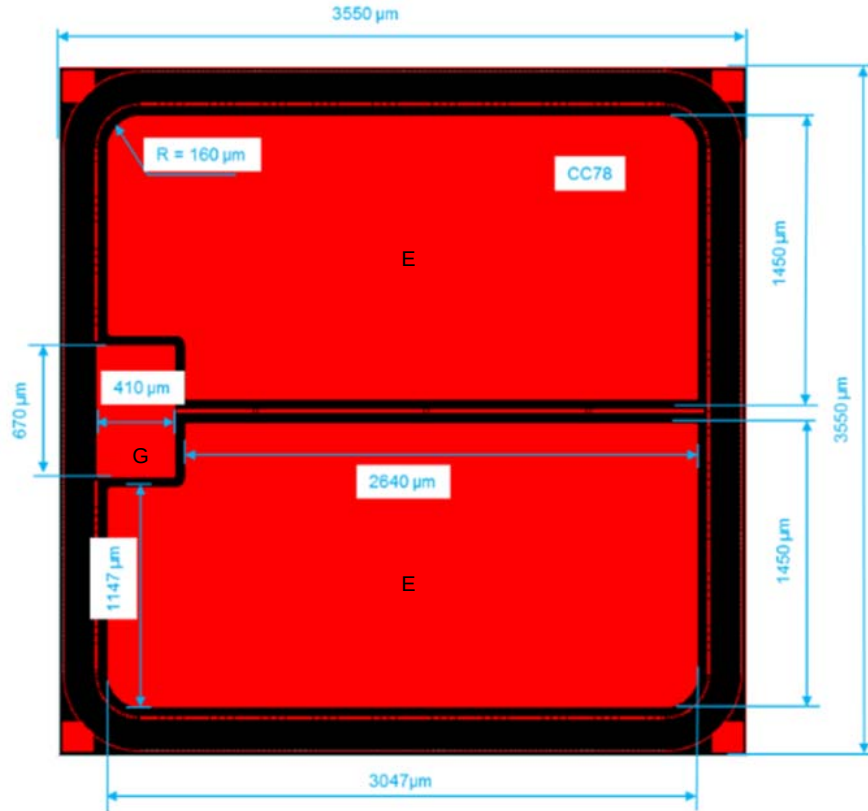
Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
STATIC CHARACTERISTICS						
Collector-Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}$, $I_C = 500\text{ }\mu\text{A}$	$V_{(BR)CES}$	650			V
Collector-Emitter Saturation Voltage	$V_{GE} = 15\text{ V}$, $I_C = 30\text{ A}$	$V_{CE(sat)}$		1.6	2.2	V
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 350\text{ }\mu\text{A}$	$V_{GE(TH)}$	4.5	5.5	6.5	V
Collector-Emitter Cutoff Current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$	I_{CES}			0.2	mA
Gate Leakage Current	$V_{GE} = 20\text{ V}$, $V_{CE} = 0\text{ V}$	I_{GES}			100	nA

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 20\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$	C_{ies}		3200		pF
Output Capacitance		C_{oes}		130		pF
Reverse Transfer Capacitance		C_{res}		85		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



E = Emitter pad
G = Gate pad
All dimensions in μm

NGTD13T65F2

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative